



ESD



TVS



TSS



MOV



GDT



PLED

AON7246E-MS Product specification

Description

The AON7246E-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

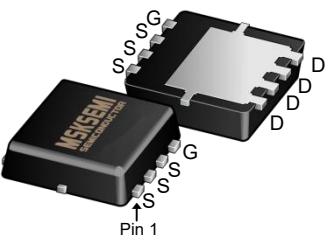
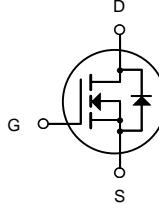
Features

- $V_{DS} = 60V$ $I_D = 40A$
- $R_{DS(ON)} < 15m\Omega$ @ $V_{GS} = 10V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Reference News

DFN3X3-8L	N-Channel MOSFET	Marking
		

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	40	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	20	A
I_{DM}	Pulsed Drain Current ²	150	A
E_{AS}	Single Pulse Avalanche Energy ³	36	mJ
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	30	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
R_{eJA}	Thermal Resistance Junction-ambient ¹	62	°C/W
R_{eJC}	Thermal Resistance Junction-Case ¹	2.5	°C/W

Electrical Characteristics (T_J=25 °C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.5	V
R _{DS(on)} note3	Static Drain-Source on-Resistance	V _{GS} =10V, I _D =20A	-	12	15	mΩ
		V _{GS} =4.5V, I _D =10A	-	15	20	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	930	-	pF
C _{oss}	Output Capacitance		-	230	-	pF
C _{rss}	Reverse Transfer Capacitance		-	8	-	pF
Q _g	Total Gate Charge	V _{DS} =30V, I _D =20A, V _{GS} =10V	-	22	-	nC
Q _{gs}	Gate-Source Charge		-	4.5	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	3.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =20A, R _G =1.6Ω, V _{GS} =10V	-	4.5	-	ns
t _r	Turn-on Rise Time		-	2.7	-	ns
t _{d(off)}	Turn-off Delay Time		-	13.8	-	ns
t _f	Turn-off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	40	-	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	150	-	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	T _J =25 °C, I=20A, dI/dt=100A/μs	-	18	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	12	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

 2. EAS condition: T_J=25 °C, V_{DD}=30V, V_G=10V, R_G=25Ω, L=0.5mH, I_{AS}=12A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure 1: Output Characteristics

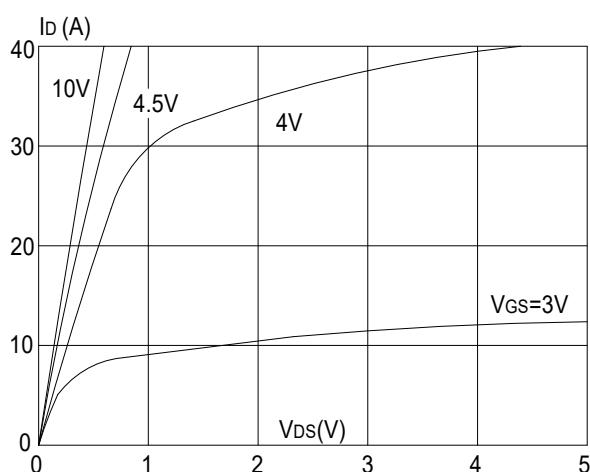


Figure 2: Typical Transfer Characteristics

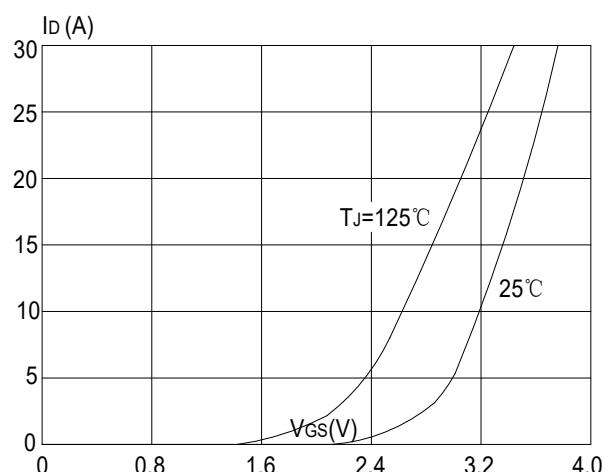


Figure 3: On-resistance vs. Drain Current

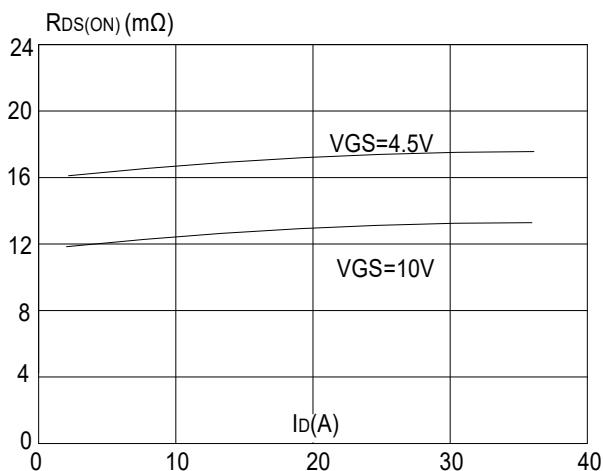


Figure 4: Body Diode Characteristics

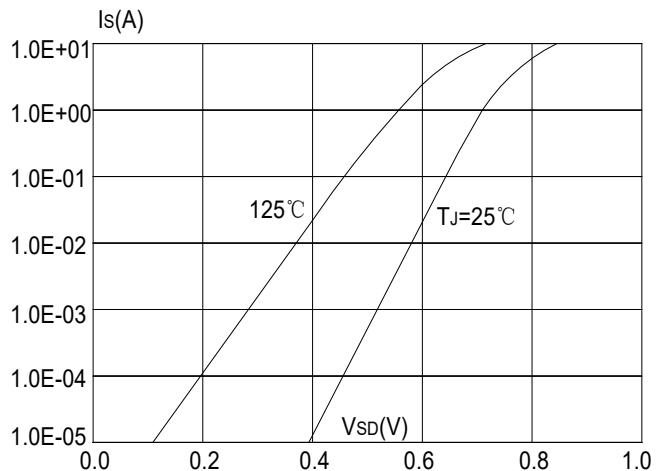


Figure 5: Gate Charge Characteristics

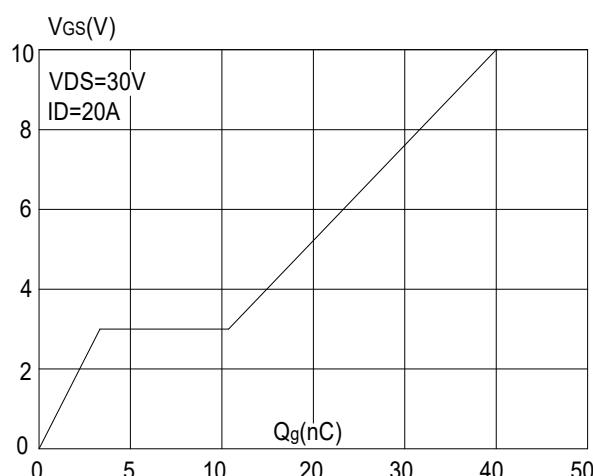


Figure 6: Capacitance Characteristics

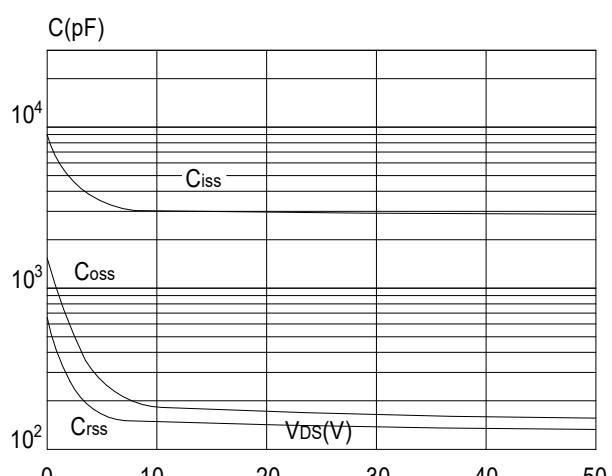


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

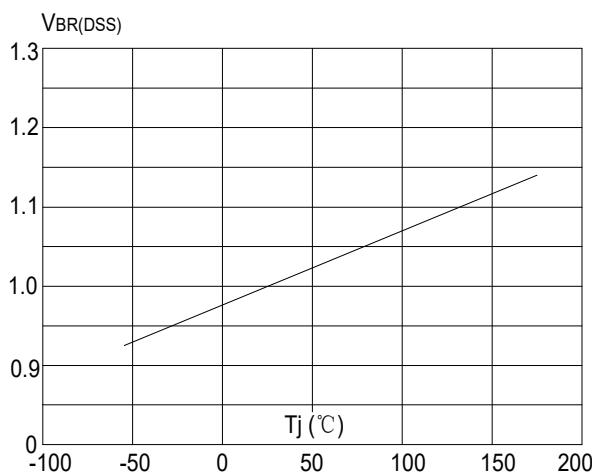


Figure 8: Normalized on Resistance vs. Junction Temperature

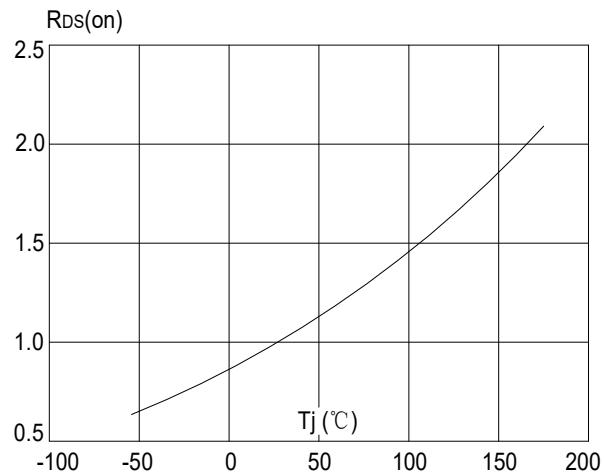


Figure 9: Maximum Safe Operating Area

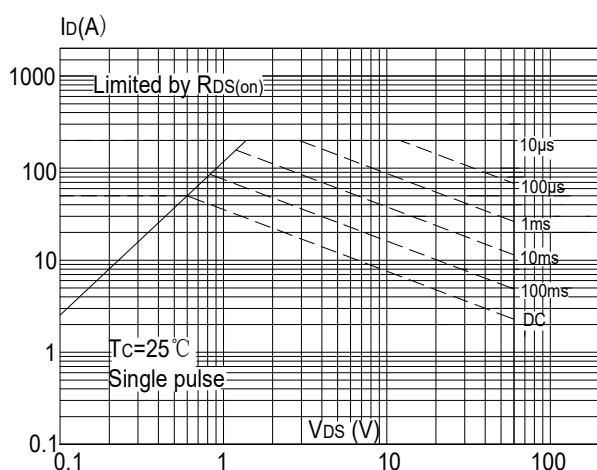


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

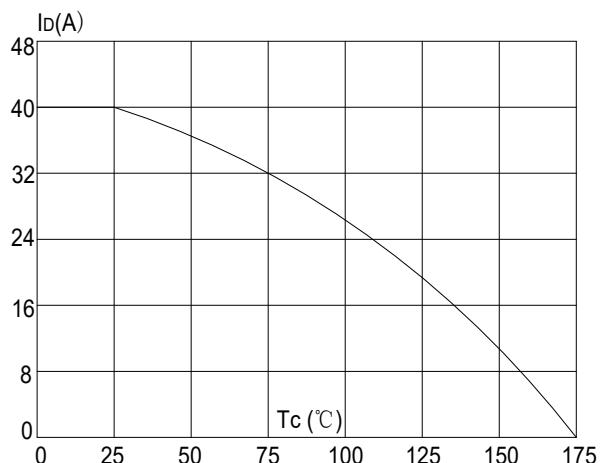
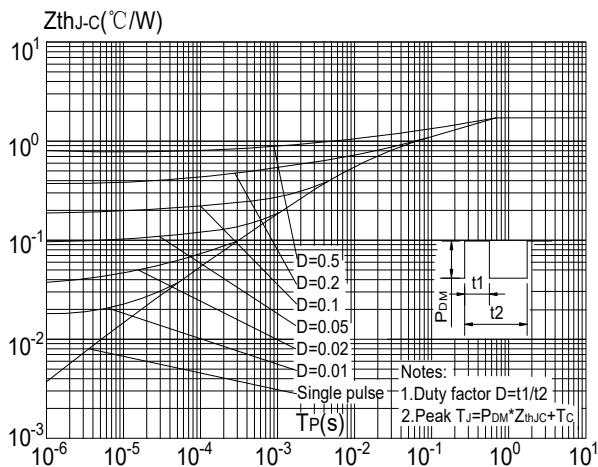
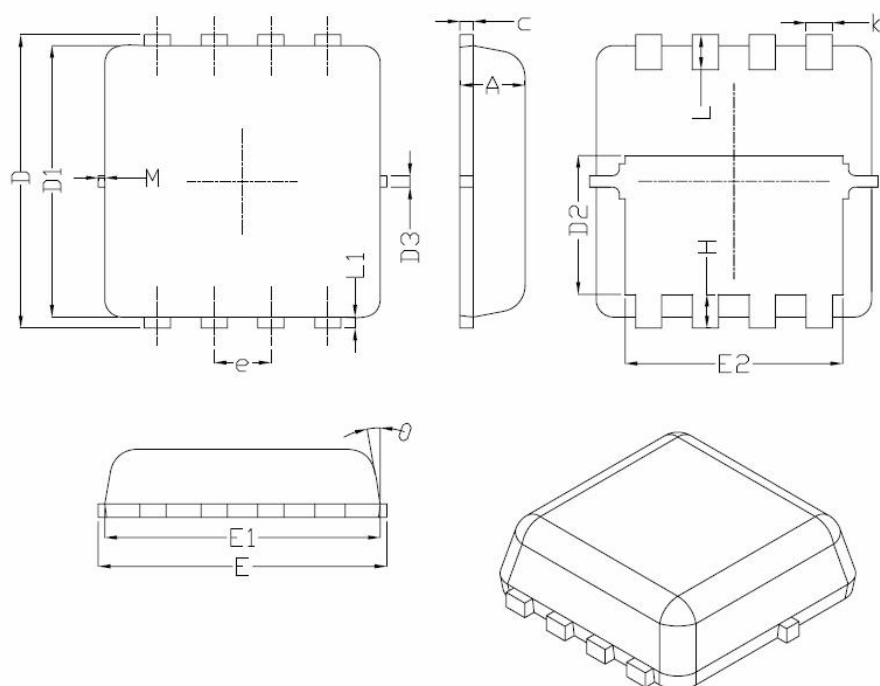


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



DFN3X3-8L Package Information


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ			10 ° 12 °

REEL SPECIFICATION

P/N	PKG	QTY
AON7246E-MS	DFN3X3-8L	5000

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